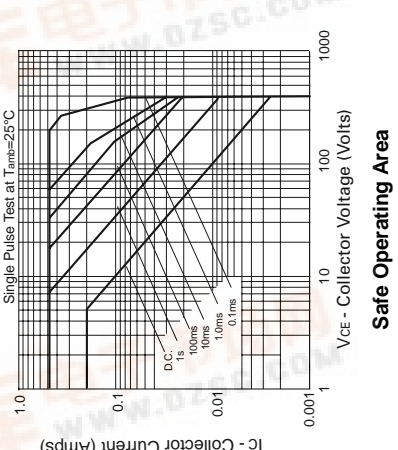
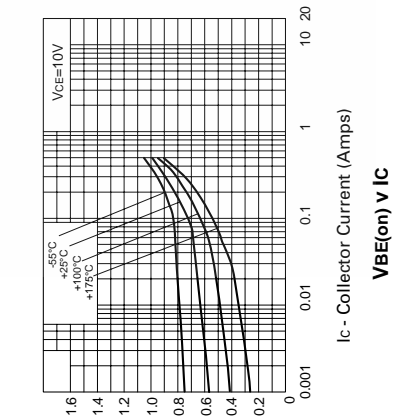
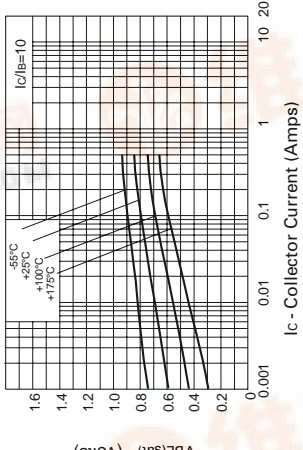
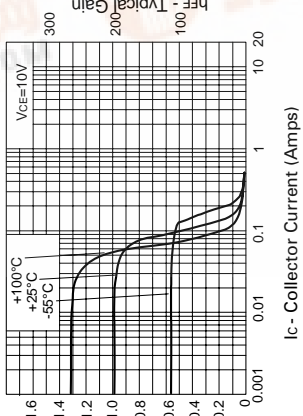
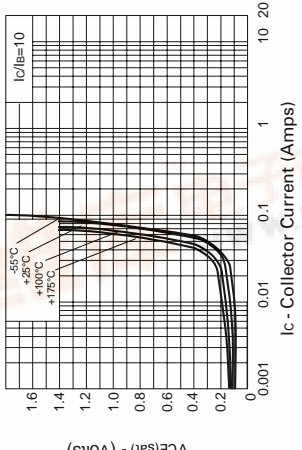
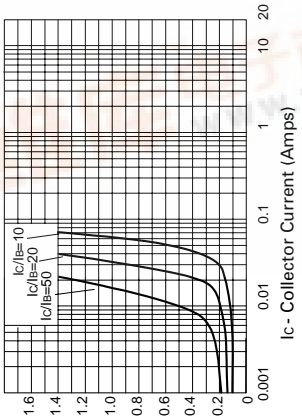




ZTX558

TYPICAL CHARACTERISTICS

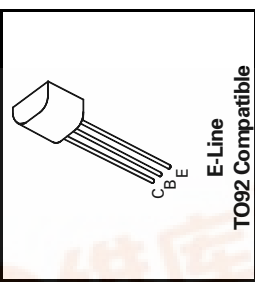


PNP SILICON PLANAR MEDIUM POWER HIGH VOLTAGE TRANSISTOR

ISSUE 1 - APRIL 94

FEATURES

- * 400 Volt V_{CEO}
- * 200mA continuous current
- * $P_{tot} = 1$ Watt



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-400	V
Collector-Emitter Voltage	V_{CEO}	-400	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-200	mA
Power Dissipation	P_{tot}	1	W
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +200	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-400			V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	$V_{BR(CEO)}$	-400			V	$I_C = -10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu A$
Collector Cut-Off Current	I_{CBO}			-100	nA	$V_{CB} = -320V$
Collector Cut-Off Current	I_{CES}			-100	nA	$V_{CE} = -320V$
Emitter Cut-Off Current	I_{EBO}			-100	nA	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.2	-0.5	V	$I_C = -20mA, I_B = -2mA$ $I_C = -50mA, I_B = -6mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9		V	$I_C = -50mA, I_B = -5mA$
Base-Emitter Turn On Voltage	$V_{BE(on)}$		-0.9		V	$I_C = -50mA, V_{CE} = -10V$
Static Forward Transfer Ratio	h_{FE}	100		300		$I_C = -1mA, V_{CE} = -10V$ $I_C = -50mA, V_{CE} = -10V$ $I_C = -100mA, V_{CE} = -10V^*$
Transition Frequency	f_T	50			MHz	$I_C = -10mA, V_{CE} = -20V$ $f = 20MHz$
Collector-Base Breakdown Voltage	C_{ob0}			5	pF	$V_{CB} = -20V, f = 1MHz$
Switching times	t_{on} t_{off}	95 1600			ns	$I_C = -50mA, V_{CE} = -100V$ $I_B = -5mA, I_B = -10mA$

* Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

查询ZTX558供应商

捷多邦, 专业PCB打样工厂, 24小时加急出货

PNP SILICON PLANAR MEDIUM POWER HIGH VOLTAGE TRANSISTOR

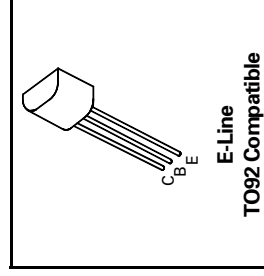
ZTX558

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ISSUE 1 – APRIL 94

FEATURES

- * 400 Volt V_{CE0}
- * 200mA continuous current
- * $P_{tot} = 1$ Watt



ABSOLUTE MAXIMUM RATINGS.

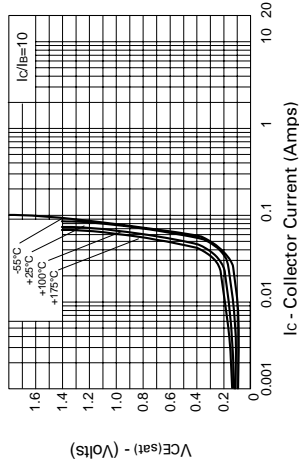
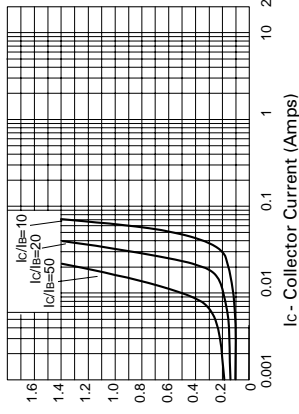
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Collector Cut-Off Current	I_{CBO}			-100	nA	$V_{CE} = -320V$
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Static Forward Current Transfer Ratio	h_{FE}	100		300		$I_C = -1mA, V_{CE} = -10V$ $I_C = -50mA, V_{CE} = -10V$ $I_C = -100mA, V_{CE} = -10V^*$
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Switching times	t_{on} t_{off}	95 1600			ns ns	$I_C = -50mA, V_{CE} = -100V$ $I_B = -5mA, I_B = -10mA$

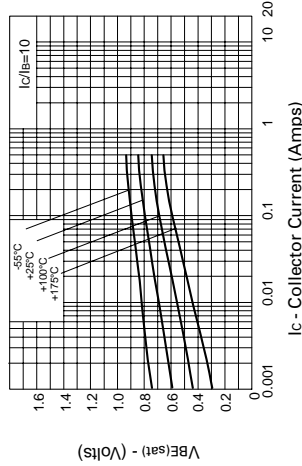
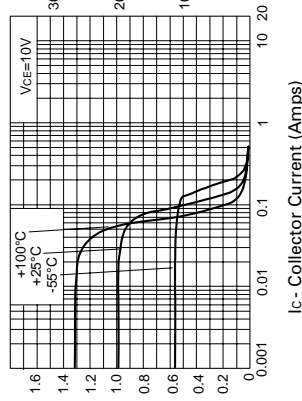
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TYPICAL CHARACTERISTICS



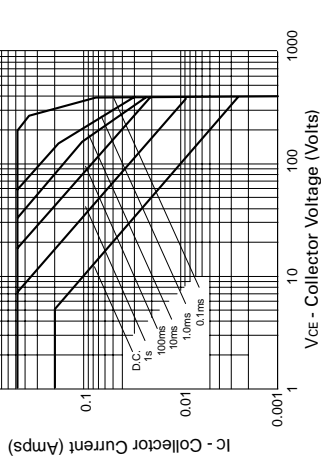
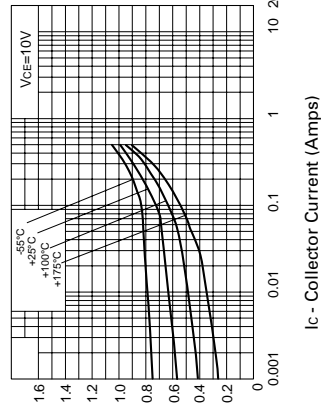
VCE(sat) v IC

VCE(sat) v IC



hFE v IC

VBE(sat) v IC



VBE(on) v IC

Safe Operating Area